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Kind regards,

Team Nexperia

PEMB17; PUMB17

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

Rev. 03 — 1 September 2009

Product data sheet

1. Product profile

1.1 General description

PNP/PNP resistor-equipped transistors

Table 1. Product overview

Type number	Package		NPN/PNP	NPN/NPN	
	NXP	JEITA	complement	complement	
PEMB17	SOT666	-	PEMD17	PEMH17	
PUMB17	SOT363	SC-88	PUMD17	PUMH17	

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current (DC)		-	-	-100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	



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PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

Pinning information 2.

Table 3 Pinning

Table 3.	riiiiiig		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		$\begin{array}{c c} & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & \\ & & & \\ & \\ & \\ & \\$
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa212

Ordering information 3.

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PEMB17	-	plastic surface mounted package; 6 leads	SOT666
PUMB17	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking 4.

Product data sheet

Marking codes Table 5.

Type number	Marking code ^[1]
PEMB17	5M
PUMB17	B*8

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
V_{I}	input voltage				
	positive		-	+10	V
	negative		-	-40	V
Io	output current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1] [2] -	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	T _{amb} ≤ 25 °C				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1] [2] _	-	625	K/W
Per device	•					
$R_{th(j-a)}$	thermal resistance from junction to ambient	$T_{amb} \le 25 ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		[1] [2] _	-	416	K/W

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, standard footprint.

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^[2] Reflow soldering is the only recommended soldering method.

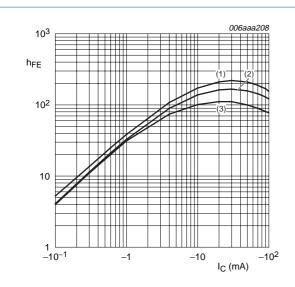
^[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified

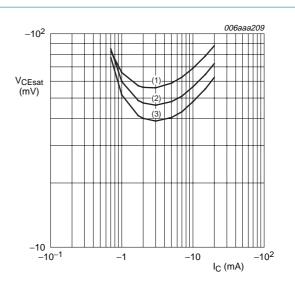
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μΑ
	cut-off current	$V_{CE} = -30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-110	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.7	-1.2	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -2 \text{ mA}$	-4	-2.7	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.37	0.47	0.57	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

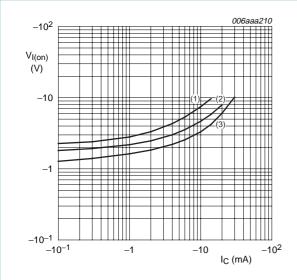
Fig 1. DC current gain as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

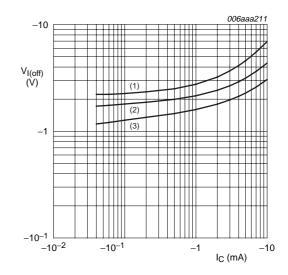
Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values





- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

- (1) $T_{amb} = -40 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 4. Off-state input voltage as a function of collector current; typical values

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Package outline 8.

SOT363 Plastic surface-mounted package; 6 leads В A = v (M) A H_{E} - ⊕ w M B е detail X **DIMENSIONS** (mm are the original dimensions)

OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT363			SC-88		$ \ \ \bigoplus \big($	04-11-08 06-03-16

e₁

ΗE

 $L_{\mathbf{p}}$

0.45

0.15

Q

0.25

у

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Fig 5. Package outline SOT363 (SC-88)

0.1

bp

0.30

0.20

0.25

0.10

D

2.2

Ε

1.35

1.15

UNIT

Product data sheet

Α

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PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

SOT666 Plastic surface-mounted package; 6 leads - A Х ΗE pin 1 index С ⊕ w M A detail X 2 mm scale **DIMENSIONS** (mm are the original dimensions) UNIT Ε D Α bp e₁ H_{E} L_{p} у 0.6 0.27 0.18 1.7 1.3 1.7 0.3 0.5 0.5 0.17 0.08 1.5 0.1 1.1 REFERENCES **EUROPEAN** OUTLINE ISSUE DATE VERSION **PROJECTION** IEC **JEDEC** JEITA 04-11-08 \bigcirc SOT666 06-03-16

Fig 6. Package outline SOT666

Product data sheet

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9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Description		ntity	
				3000	4000	10000
PEMB17	SOT666	4 mm pitch, 8 mm tape and reel;		-	-115	-
PUMB17	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-135
PUMB17	SOT363	4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

PEMB17; PUMB17

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

10. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB17_PUMB17_3	20090901	Product data sheet	-	PEMB17_PUMB17_2		
Modifications:	 This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. 					
	Figure 5 "Page	ckage outline SOT363 (SC-	88)": updated			
	 Figure 6 "Page 	ckage outline SOT666": upo	dated			
PEMB17_PUMB17_2	20050203	Product data sheet	-	PUMB17_1		
PUMB17_1	20031103	Product specification	-	-		

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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12. Contact information

Product data sheet

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Date of release: 1 September 2009

Document identifier: PEMB17_PUMB17_3

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